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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, SD, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	66
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 32x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk64fn1m0vll12r

2.2.5 Power consumption operating behaviors

NOTE

The maximum values represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash					2
	• @ 1.8V	—	31.1	36.65	mA	
	• @ 3.0V	—	31	36.75	mA	
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash					3, 4
	• @ 1.8V	—	42.7	48.35	mA	
	• @ 3.0V					
	• @ 25°C	—	40	41.60	mA	
	• @ 105°C	—	48.33	51.50	mA	
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	17.9	—	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	6.9	—	mA	5
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	1.0	—	mA	6
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	1.7	—	mA	7
I_{DD_VLPW}	Very-low-power wait mode current at 3.0 V — all peripheral clocks disabled	—	0.678	—	mA	8
I_{DD_STOP}	Stop mode current at 3.0 V					
	• @ –40 to 25°C	—	0.49	1.24	mA	
	• @ 70°C	—	1.18	4.3	mA	
	• @ 105°C	—	3.0	12.5	mA	
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V					
	• @ –40 to 25°C	—	57	139.31	µA	
	• @ 70°C	—	291	679.33	µA	
	• @ 105°C	—	927.3	1869.85	µA	
I_{DD_LLS}	Low leakage stop mode current at 3.0 V					9

Table continues on the next page...

- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFE

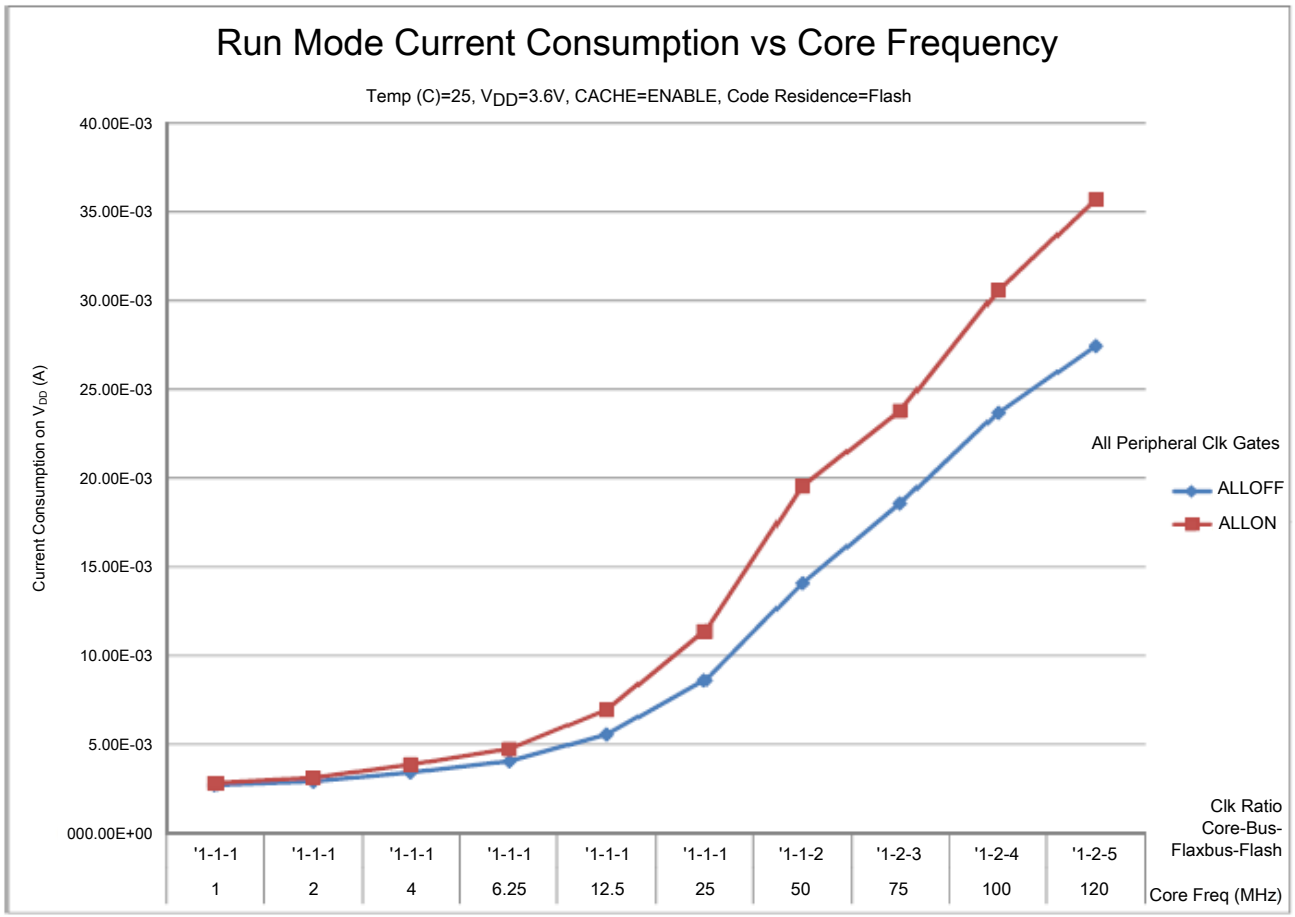

Figure 3. Run mode supply current vs. core frequency

Wideband TEM Cell Method. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

2. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = 12 MHz (crystal), f_{SYS} = 96 MHz, f_{BUS} = 48MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

2.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.nxp.com.
2. Perform a keyword search for "EMC design."

2.2.8 Capacitance attributes

Table 9. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

2.3 Switching specifications

2.3.1 Device clock specifications

Table 10. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	120	MHz	
	System and core clock when Full Speed USB in operation	20	—	MHz	
f_{ENET}	System and core clock when ethernet in operation • 10 Mbps • 100 Mbps	 5 50	 — —	MHz	
f_{BUS}	Bus clock	—	60	MHz	
FB_CLK	FlexBus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	

Table continues on the next page...

Table 10. Device clock specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
f_{LPTMR}	LPTMR clock	—	25	MHz	
VLPR mode[1]					
f_{SYS}	System and core clock	—	4	MHz	
f_{BUS}	Bus clock	—	4	MHz	
FB_CLK	FlexBus clock	—	4	MHz	
f_{FLASH}	Flash clock	—	0.8	MHz	
f_{ERCLK}	External reference clock	—	16	MHz	
f_{LPTMR_pin}	LPTMR clock	—	25	MHz	
f_{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz	
$f_{FlexCAN\_ERCLK}$	FlexCAN external reference clock	—	8	MHz	
f_{I2S_MCLK}	I2S master clock	—	12.5	MHz	
f_{I2S_BCLK}	I2S bit clock	—	4	MHz	

1. The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

2.3.2 General switching specifications

These general purpose specifications apply to all signals configured for GPIO, UART, CAN, CMT, IEEE 1588 timer, timers, and I^2C signals.

Table 11. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1, 2
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter enabled) — Asynchronous path	100	—	ns	3
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) — Asynchronous path	50	—	ns	3
	External reset pulse width (digital glitch filter disabled)	100	—	ns	3
	Mode select ($\overline{EZP\_CS}$) hold time after reset deassertion	2	—	Bus clock cycles	
	Port rise and fall time (high drive strength) - 3 V				4
	• Slew disabled				
	• $1.71 \le V_{DD} \le 2.7V$	—	8	ns	
	• $2.7 \le V_{DD} \le 3.6V$	—	6	ns	
	• Slew enabled				
		—	18	ns	

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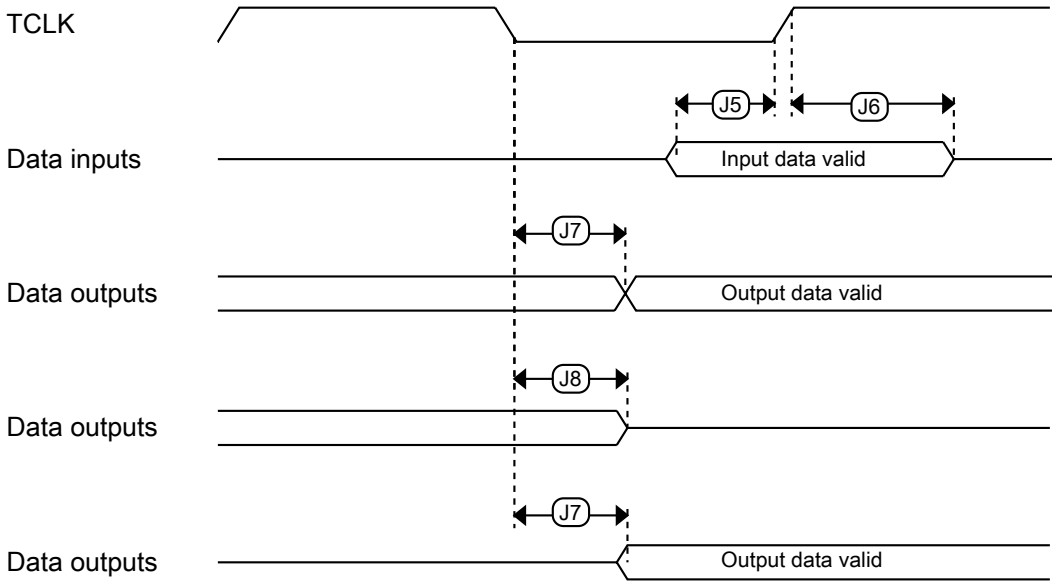

Figure 8. Boundary scan (JTAG) timing

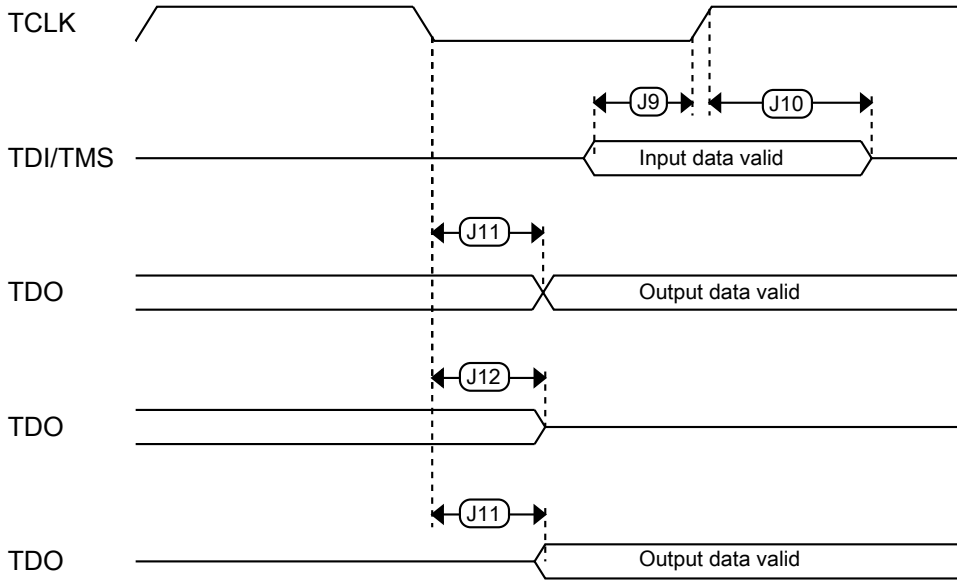

Figure 9. Test Access Port timing

Table 21. 32kHz oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
C_{para}	Parasitical capacitance of EXTAL32 and XTAL32	—	5	7	pF
V_{pp}[1]	Peak-to-peak amplitude of oscillation	—	0.6	—	V

1. When a crystal is being used with the 32 kHz oscillator, the EXTAL32 and XTAL32 pins should only be connected to required oscillator components and must not be connected to any other devices.

3.3.4.2 32 kHz oscillator frequency specifications

Table 22. 32 kHz oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal	—	32.768	—	kHz	
t_{start}	Crystal start-up time	—	1000	—	ms	1
$f_{ec\_extal32}$	Externally provided input clock frequency	—	32.768	—	kHz	2
$v_{ec\_extal32}$	Externally provided input clock amplitude	700	—	V_{BAT}	mV	2, 3

1. Proper PC board layout procedures must be followed to achieve specifications.
2. This specification is for an externally supplied clock driven to EXTAL32 and does not apply to any other clock input. The oscillator remains enabled and XTAL32 must be left unconnected.
3. The parameter specified is a peak-to-peak value and V_{IH} and V_{IL} specifications do not apply. The voltage of the applied clock must be within the range of V_{SS} to V_{BAT}.

3.4 Memories and memory interfaces

3.4.1 Flash (FTFE) electrical specifications

This section describes the electrical characteristics of the FTFE module.

3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 23. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm8}	Program Phrase high-voltage time	—	7.5	18	µs	
$t_{hversscr}$	Erase Flash Sector high-voltage time	—	13	113	ms	1
$t_{hversblk128k}$	Erase Flash Block high-voltage time for 128 KB	—	104	904	ms	1
$t_{hversblk512k}$	Erase Flash Block high-voltage time for 512 KB	—	416	3616	ms	1

1. Maximum time based on expectations at cycling end-of-life.

3.4.1.2 Flash timing specifications — commands

Table 24. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Read 1s Block execution time					
$t_{rd1blk128k}$	• 128 KB data flash	—	—	0.5	ms	
$t_{rd1blk512k}$	• 512 KB program flash	—	—	1.8	ms	
$t_{rd1sec4k}$	Read 1s Section execution time (4 KB flash)	—	—	100	µs	1
t_{pgmchk}	Program Check execution time	—	—	95	µs	1
t_{rdrsrc}	Read Resource execution time	—	—	40	µs	1
t_{pgm8}	Program Phrase execution time	—	90	150	µs	
	Erase Flash Block execution time					2
$t_{ersblk128k}$	• 128 KB data flash	—	110	925	ms	
$t_{ersblk512k}$	• 512 KB program flash	—	435	3700	ms	
t_{ersscr}	Erase Flash Sector execution time	—	15	115	ms	2
$t_{pgmsec1k}$	Program Section execution time (1KB flash)	—	5	—	ms	
	Read 1s All Blocks execution time					
$t_{rd1allx}$	• FlexNVM devices	—	—	2.2	ms	
$t_{rd1alln}$	• Program flash only devices	—	—	3.4	ms	
t_{rdonce}	Read Once execution time	—	—	30	µs	1
$t_{pgmonce}$	Program Once execution time	—	70	—	µs	
t_{ersall}	Erase All Blocks execution time	—	870	7400	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	µs	1
	Swap Control execution time					
$t_{swapx01}$	• control code 0x01	—	200	—	µs	
$t_{swapx02}$	• control code 0x02	—	70	150	µs	
$t_{swapx04}$	• control code 0x04	—	70	150	µs	
$t_{swapx08}$	• control code 0x08	—	—	30	µs	
	Program Partition for EEPROM execution time					
$t_{pgmpart32k}$	• 32 KB FlexNVM	—	70	—	ms	
$t_{pgmpart128k}$	• 128 KB FlexNVM	—	75	—	ms	
	Set FlexRAM Function execution time:					
$t_{setramff}$	• Control Code 0xFF	—	70	—	µs	
$t_{setram32k}$	• 32 KB EEPROM backup	—	0.8	1.2	ms	
$t_{setram64k}$	• 64 KB EEPROM backup	—	1.3	1.9	ms	
$t_{setram128k}$	• 128 KB EEPROM backup	—	2.4	3.1	ms	

Table continues on the next page...

Table 24. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{eewr8bers}$	Byte-write to erased FlexRAM location execution time	—	175	275	µs	3
	Byte-write to FlexRAM execution time:					
$t_{eewr8b32k}$	• 32 KB EEPROM backup	—	385	1700	µs	
$t_{eewr8b64k}$	• 64 KB EEPROM backup	—	475	2000	µs	
$t_{eewr8b128k}$	• 128 KB EEPROM backup	—	650	2350	µs	
$t_{eewr16bers}$	16-bit write to erased FlexRAM location execution time	—	175	275	µs	
	16-bit write to FlexRAM execution time:					
$t_{eewr16b32k}$	• 32 KB EEPROM backup	—	385	1700	µs	
$t_{eewr16b64k}$	• 64 KB EEPROM backup	—	475	2000	µs	
$t_{eewr16b128k}$	• 128 KB EEPROM backup	—	650	2350	µs	
$t_{eewr32bers}$	32-bit write to erased FlexRAM location execution time	—	360	550	µs	
	32-bit write to FlexRAM execution time:					
$t_{eewr32b32k}$	• 32 KB EEPROM backup	—	630	2000	µs	
$t_{eewr32b64k}$	• 64 KB EEPROM backup	—	810	2250	µs	
$t_{eewr32b128k}$	• 128 KB EEPROM backup	—	1200	2650	µs	

1. Assumes 25MHz or greater flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

3.4.1.3 Flash high voltage current behaviors

Table 25. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	3.5	7.5	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 26. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	

Table continues on the next page...

Table 26. NVM reliability specifications (continued)

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2
Data Flash						
$t_{nvmretd10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretd1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycd}$	Cycling endurance	10 K	50 K	—	cycles	2
FlexRAM as EEPROM						
$t_{nvmretee100}$	Data retention up to 100% of write endurance	5	50	—	years	
$t_{nvmretee10}$	Data retention up to 10% of write endurance	20	100	—	years	
$n_{nvmcycee}$	Cycling endurance for EEPROM backup	20 K	50 K	—	cycles	2
	Write endurance					3
$n_{nvmwree16}$	• EEPROM backup to FlexRAM ratio = 16	140 K	400 K	—	writes	
$n_{nvmwree128}$	• EEPROM backup to FlexRAM ratio = 128	1.26 M	3.2 M	—	writes	
$n_{nvmwree512}$	• EEPROM backup to FlexRAM ratio = 512	5 M	12.8 M	—	writes	
$n_{nvmwree2k}$	• EEPROM backup to FlexRAM ratio = 2,048	20 M	50 M	—	writes	
$n_{nvmwree4k}$	• EEPROM backup to FlexRAM ratio = 4,096	40 M	100 M	—	writes	

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at -40°C ≤ T_j ≤ 125°C.
3. Write endurance represents the number of writes to each FlexRAM location at -40°C ≤Tj ≤ 125°C influenced by the cycling endurance of the FlexNVM and the allocated EEPROM backup per subsystem. Minimum and typical values assume all 16-bit or 32-bit writes to FlexRAM; all 8-bit writes result in 50% less endurance.

3.4.1.5 Write endurance to FlexRAM for EEPROM

When the FlexNVM partition code is not set to full data flash, the EEPROM data set size can be set to any of several non-zero values.

The bytes not assigned to data flash via the FlexNVM partition code are used by the FTFE to obtain an effective endurance increase for the EEPROM data. The built-in EEPROM record management system raises the number of program/erase cycles that can be attained prior to device wear-out by cycling the EEPROM data through a larger EEPROM NVM storage space.

While different partitions of the FlexNVM are available, the intention is that a single choice for the FlexNVM partition code and EEPROM data set size is used throughout the entire lifetime of a given application. The EEPROM endurance equation and graph shown below assume that only one configuration is ever used.

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

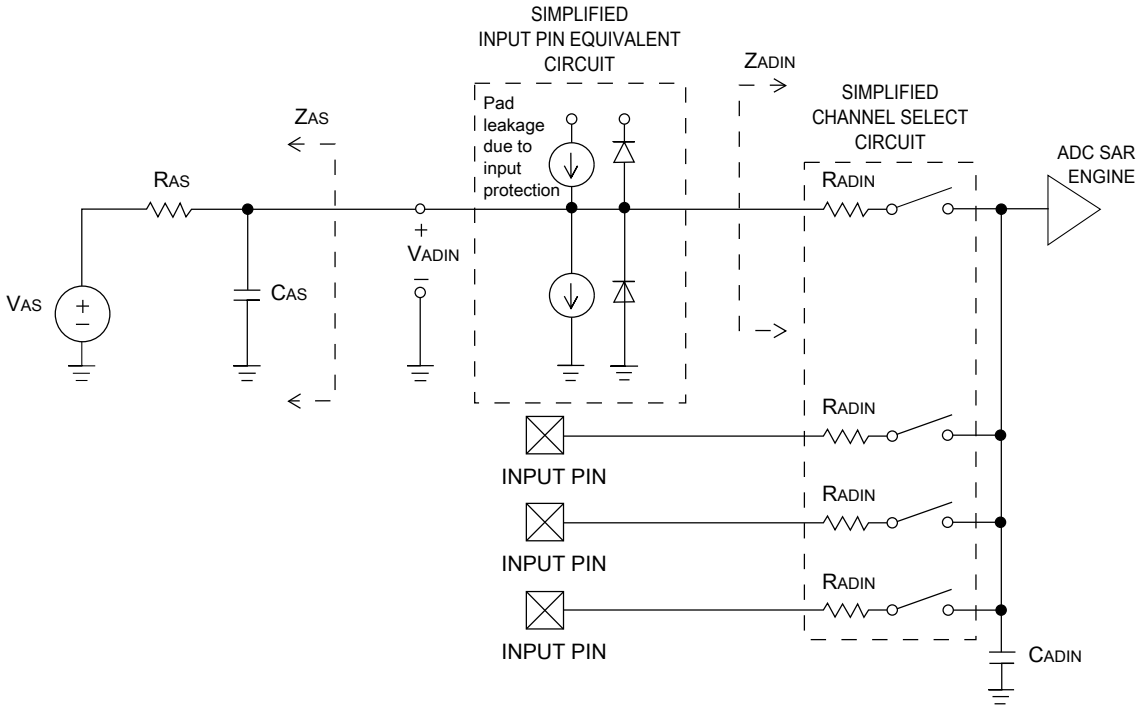

Figure 15. ADC input impedance equivalency diagram

3.6.1.2 16-bit ADC electrical characteristics

Table 31. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0	1.2	2.4	3.9	MHz	t_{ADACK} = 1/ f_{ADACK}
		• ADLPC = 1, ADHSC = 1	2.4	4.0	6.1	MHz	
		• ADLPC = 0, ADHSC = 0	3.0	5.2	7.3	MHz	
		• ADLPC = 0, ADHSC = 1	4.4	6.2	9.5	MHz	
	Sample Time	See Reference Manual chapter for sample times					

Table continues on the next page...

6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

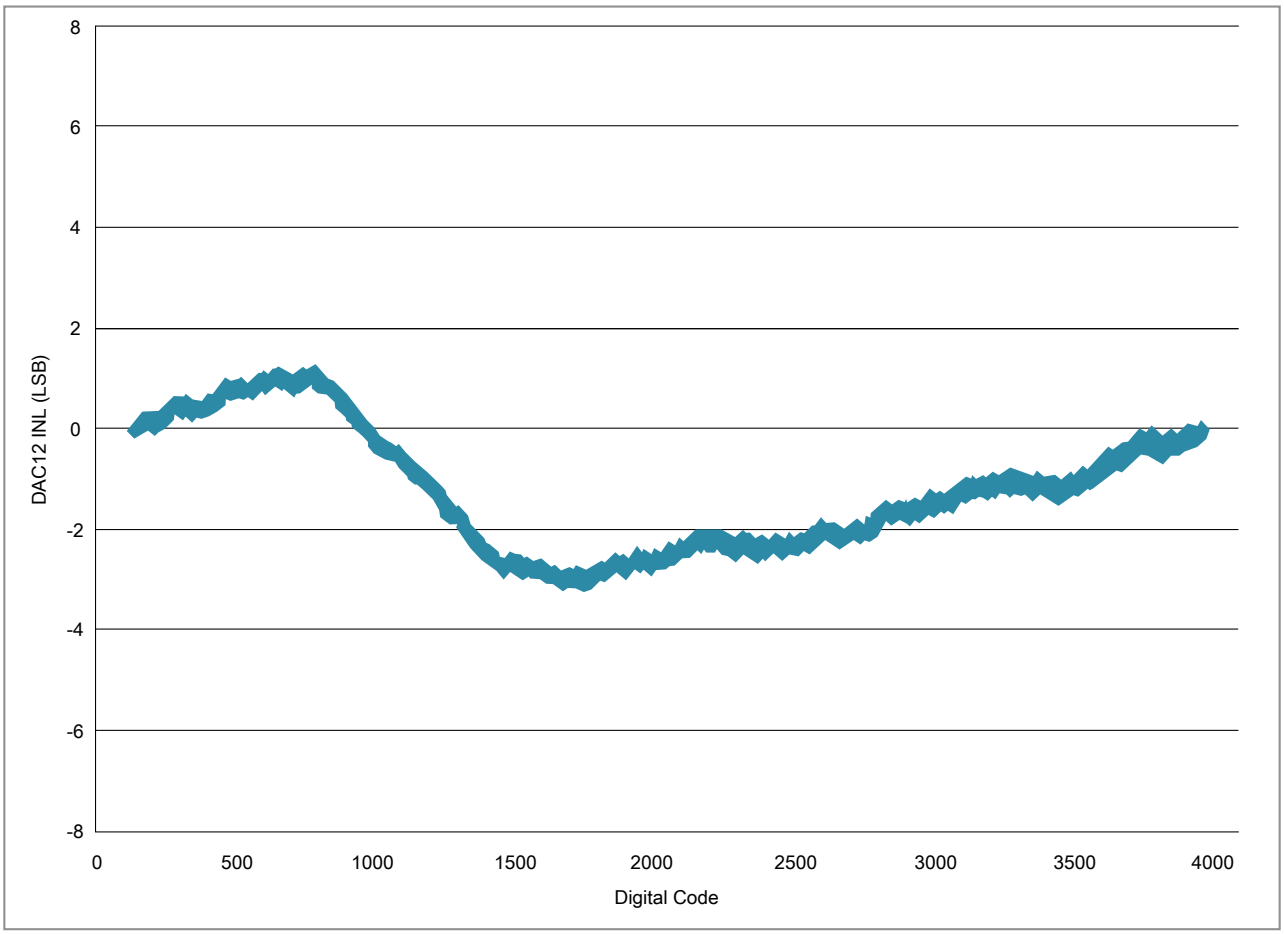

Figure 20. Typical INL error vs. digital code

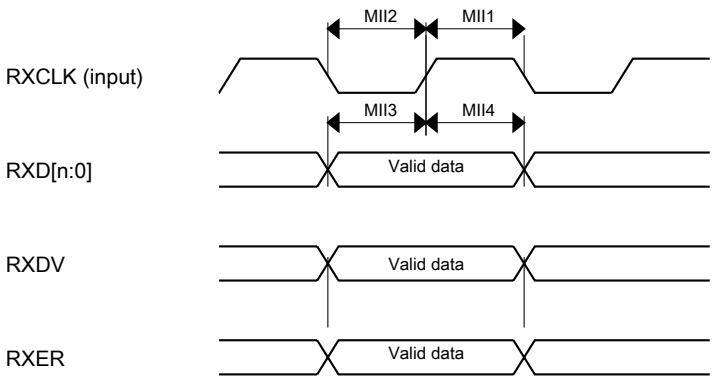

Figure 23. RMII/MII receive signal timing diagram

3.8.1.2 RMII signal switching specifications

The following timing specs meet the requirements for RMII style interfaces for a range of transceiver devices.

Table 40. RMII signal switching specifications

Num	Description	Min.	Max.	Unit
—	EXTAL frequency (RMII input clock RMII_CLK)	—	50	MHz
RMII1	RMII_CLK pulse width high	35%	65%	RMII_CLK period
RMII2	RMII_CLK pulse width low	35%	65%	RMII_CLK period
RMII3	RXD[1:0], CRS_DV, RXER to RMII_CLK setup	4	—	ns
RMII4	RMII_CLK to RXD[1:0], CRS_DV, RXER hold	2	—	ns
RMII7	RMII_CLK to TXD[1:0], TXEN invalid	4	—	ns
RMII8	RMII_CLK to TXD[1:0], TXEN valid	—	15	ns

3.8.1.3 MDIO serial management timing specifications

Table 41. MDIO serial management channel signal timing

Num	Characteristic	Symbol	Min	Max	Unit
E10	MDC cycle time	t_{MDC}	400	—	ns
E11	MDC pulse width		40	60	% t_{MDC}
E12	MDC to MDIO output valid		—	375	ns
E13	MDC to MDIO output invalid		25	—	ns
E14	MDIO input to MDC setup		10	—	ns
E15	MDIO input to MDC hold		0	—	ns

3.8.7 DSPI switching specifications (full voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provides DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 46. Master mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	1
	Frequency of operation	—	15	MHz	
DS1	DSPI_SCK output cycle time	4 x t_{BUS}	—	ns	
DS2	DSPI_SCK output high/low time	(t_{SCK}/2) - 4	($t_{SCK/2}$) + 4	ns	
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	(t_{BUS} x 2) – 4	—	ns	2
DS4	DSPI_SCK to DSPI_PCS*n* invalid delay	(t_{BUS} x 2) – 4	—	ns	3
DS5	DSPI_SCK to DSPI_SOUT valid	—	10	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-4.5	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	21	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The DSPI module can operate across the entire operating voltage for the processor, but to run across the full voltage range the maximum frequency of operation is reduced.
2. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
3. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

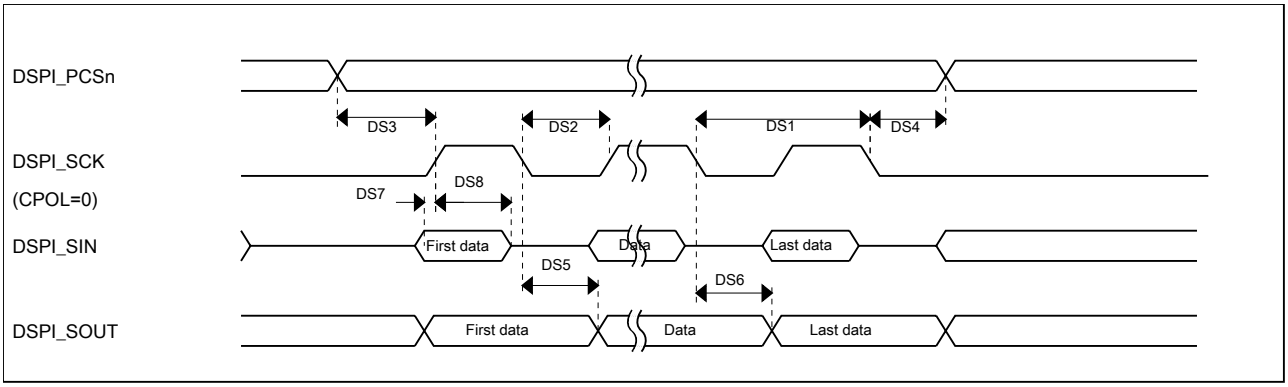

Figure 27. DSPI classic SPI timing — master mode

Table 47. Slave mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V

Table continues on the next page...

Table 47. Slave mode DSPI timing (full voltage range) (continued)

Num	Description	Min.	Max.	Unit
	Frequency of operation	—	7.5	MHz
DS9	DSPI_SCK input cycle time	8 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	(t_{SCK}/2) - 4	($t_{SCK/2}$) + 4	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	23.5	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	4	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	21	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	19	ns

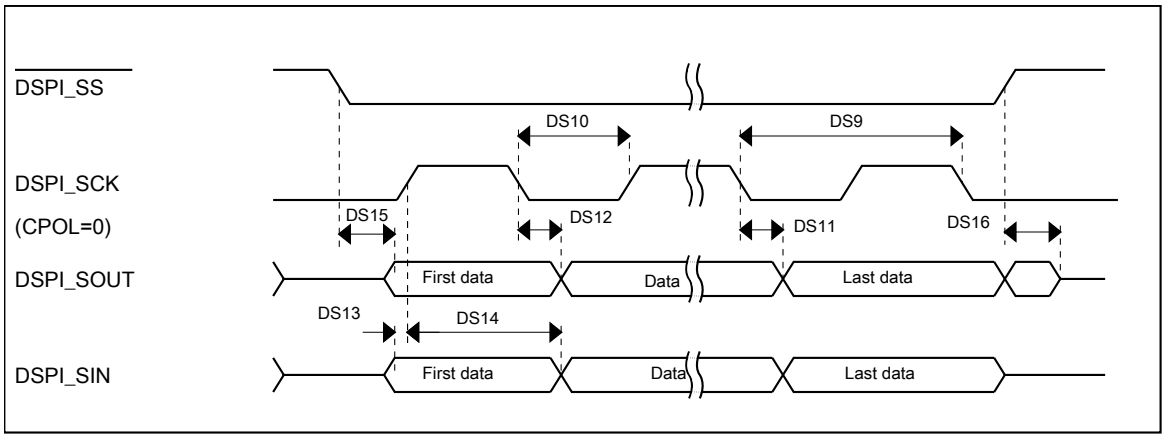

Figure 28. DSPI classic SPI timing — slave mode

3.8.8 Inter-Integrated Circuit Interface (I^2C) timing

Table 48. I^2C timing

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f_{SCL}	0	100	0	400[1]	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t_{HD}; STA	4	—	0.6	—	µs
LOW period of the SCL clock	t_{LOW}	4.7	—	1.25	—	µs
HIGH period of the SCL clock	t_{HIGH}	4	—	0.6	—	µs
Set-up time for a repeated START condition	t_{SU}; STA	4.7	—	0.6	—	µs
Data hold time for I^2C bus devices	t_{HD}; DAT	0[2]	3.45[3]	0[4]	0.9[2]	µs

Table continues on the next page...

2. C_b = total capacitance of the one bus line in pF.

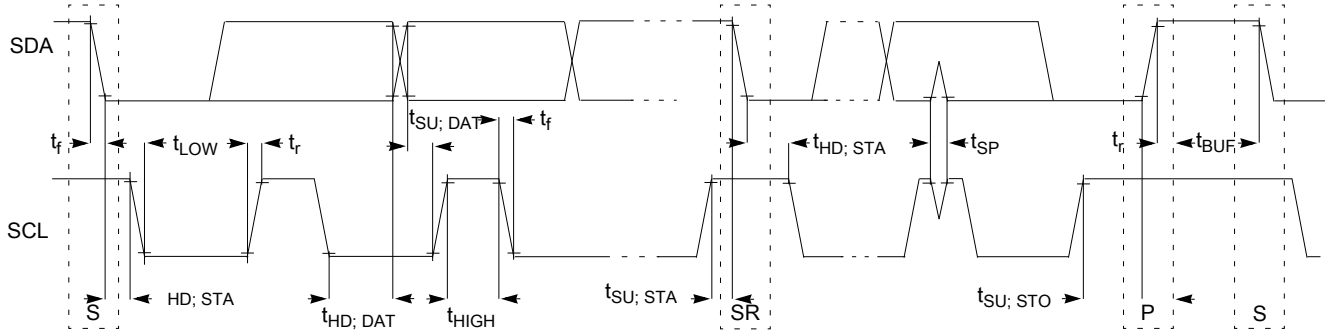

Figure 29. Timing definition for devices on the I²C bus

3.8.9 UART switching specifications

See General switching specifications.

3.8.10 SDHC specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

Table 50. SDHC switching specifications

Num	Symbol	Description	Min.	Max.	Unit
		Operating voltage	1.71	3.6	V
	Card input clock				
SD1	fpp	Clock frequency (low speed)	0	400	kHz
	fpp	Clock frequency (SD\SDIO full speed\high speed)	0	25\50	MHz
	fpp	Clock frequency (MMC full speed\high speed)	0	20\50	MHz
	f_{OD}	Clock frequency (identification mode)	0	400	kHz
SD2	t_{WL}	Clock low time	7	—	ns
SD3	t_{WH}	Clock high time	7	—	ns
SD4	t_{TLH}	Clock rise time	—	3	ns
SD5	t_{THL}	Clock fall time	—	3	ns
	SDHC output / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)				
SD6	t_{OD}	SDHC output delay (output valid)	-5	8.3	ns
	SDHC input / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)				
SD7	t_{ISU}	SDHC input setup time	5.5	—	ns
SD8	t_{IH}	SDHC input hold time	0	—	ns

144 QFP	144 MAP BGA	100 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	ALT8	ALT9
28	L2	19	ADC0_ DM0/ ADC1_ DM3	ADC0_ DM0/ ADC1_ DM3										
29	M1	20	ADC1_ DP0/ ADC0_DP3	ADC1_ DP0/ ADC0_DP3										
30	M2	21	ADC1_ DM0/ ADC0_ DM3	ADC1_ DM0/ ADC0_ DM3										
31	H5	22	VDDA	VDDA										
32	G5	23	VREFH	VREFH										
33	G6	24	VREFL	VREFL										
34	H6	25	VSSA	VSSA										
35	K3	—	ADC1_ SE16/ CMP2_IN2/ ADC0_ SE22	ADC1_ SE16/ CMP2_IN2/ ADC0_ SE22										
36	J3	—	ADC0_ SE16/ CMP1_IN2/ ADC0_ SE21	ADC0_ SE16/ CMP1_IN2/ ADC0_ SE21										
37	M3	26	VREF_ OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_ SE18	VREF_ OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_ SE18										
38	L3	27	DAC0_ OUT/ CMP1_IN3/ ADC0_ SE23	DAC0_ OUT/ CMP1_IN3/ ADC0_ SE23										
39	L4	—	DAC1_ OUT/ CMP0_IN4/ CMP2_IN3/ ADC1_ SE23	DAC1_ OUT/ CMP0_IN4/ CMP2_IN3/ ADC1_ SE23										
40	M7	28	XTAL32	XTAL32										
41	M6	29	EXTAL32	EXTAL32										
42	L6	30	VBAT	VBAT										
43	—	—	VDD	VDD										
44	—	—	VSS	VSS										

144 QFP	144 MAP BGA	100 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	ALT8	ALT9
45	M4	31	ADC0_ SE17	ADC0_ SE17	PTE24		UART4_TX		I2C0_SCL	EWM_ OUT_b				
46	K5	32	ADC0_ SE18	ADC0_ SE18	PTE25/ x_LLWU_ P21		UART4_ RX		I2C0_SDA	EWM_IN			x_LLWU_ P21	
47	K4	33	DISABLED		PTE26	ENET_ 1588_ CLKIN	UART4_ CTS_b			RTC_ CLKOUT	USB_ CLKIN			
48	J4	—	DISABLED		PTE27		UART4_ RTS_b							
49	H4	—	DISABLED		PTE28									
50	J5	34	JTAG_ TCLK/ SWD_CLK/ EZP_CLK		PTA0	UART0_ CTS_b/ UART0_ COL_b	FTM0_CH5				JTAG_ TCLK/ SWD_CLK			EZP_CLK
51	J6	35	JTAG_TDI/ EZP_DI		PTA1	UART0_ RX	FTM0_CH6				JTAG_TDI			EZP_DI
52	K6	36	JTAG_ TDO/ TRACE_ SWO/ EZP_DO		PTA2	UART0_TX	FTM0_CH7				JTAG_ TDO/ TRACE_ SWO			EZP_DO
53	K7	37	JTAG_ TMS/ SWD_DIO		PTA3	UART0_ RTS_b	FTM0_CH0				JTAG_ TMS/ SWD_DIO			
54	L7	38	NMI_b/ EZP_CS_b		PTA4/ LLWU_P3		FTM0_CH1				NMI_b		LLWU_P3	EZP_CS_b
55	M8	39	DISABLED		PTA5	USB_ CLKIN	FTM0_CH2	RMII0_ RXER/ MII0_ RXER	CMP2_ OUT	I2S0_TX_ BCLK	JTAG_ TRST_b			
56	E7	40	VDD	VDD										
57	G7	41	VSS	VSS										
58	J7	—	DISABLED		PTA6		FTM0_CH3		CLKOUT		TRACE_ CLKOUT			
59	J8	—	ADC0_ SE10	ADC0_ SE10	PTA7		FTM0_CH4				TRACE_ D3			
60	K8	—	ADC0_ SE11	ADC0_ SE11	PTA8		FTM1_CH0			FTM1_ QD_PHA	TRACE_ D2			
61	L8	—	DISABLED		PTA9		FTM1_CH1	MII0_RXD3		FTM1_ QD_PHB	TRACE_ D1			
62	M9	—	DISABLED		PTA10/ x_LLWU_ P22		FTM2_CH0	MII0_RXD2		FTM2_ QD_PHA	TRACE_ D0		x_LLWU_ P22	
63	L9	—	DISABLED		PTA11/ x_LLWU_ P23		FTM2_CH1	MII0_ RXCLK	I2C2_SDA	FTM2_ QD_PHB			x_LLWU_ P23	

144 QFP	144 MAP BGA	100 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	ALT8	ALT9
									8_BLS23_16_b					
126	B5	—	DISABLED		PTC19		UART3_CTS_b	ENET0_1588_TMR3	FB_CS3_b/FB_BE7_0_BLS31_24_b	FB_TA_b				
127	A5	93	DISABLED		PTD0/LLWU_P12	SPI0_PCS0	UART2_RTS_b	FTM3_CH0	FB_ALE/FB_CS1_b/FB_TS_b				LLWU_P12	
128	D4	94	ADC0_SE5b	ADC0_SE5b	PTD1	SPI0_SCK	UART2_CTS_b	FTM3_CH1	FB_CS0_b					
129	C4	95	DISABLED		PTD2/LLWU_P13	SPI0_SOUT	UART2_RX	FTM3_CH2	FB_AD4		I2C0_SCL		LLWU_P13	
130	B4	96	DISABLED		PTD3	SPI0_SIN	UART2_TX	FTM3_CH3	FB_AD3		I2C0_SDA			
131	A4	97	DISABLED		PTD4/LLWU_P14	SPI0_PCS1	UART0_RTS_b	FTM0_CH4	FB_AD2	EWM_IN	SPI1_PCS0		LLWU_P14	
132	A3	98	ADC0_SE6b	ADC0_SE6b	PTD5	SPI0_PCS2	UART0_CTS_b/UART0_COL_b	FTM0_CH5	FB_AD1	EWM_OUT_b	SPI1_SCK			
133	A2	99	ADC0_SE7b	ADC0_SE7b	PTD6/LLWU_P15	SPI0_PCS3	UART0_RX	FTM0_CH6	FB_AD0	FTM0_FLT0	SPI1_SOUT		LLWU_P15	
134	M10	—	VSS	VSS										
135	F8	—	VDD	VDD										

5.2 Unused analog interfaces

Table 57. Unused analog interfaces

Module name	Pins	Recommendation if unused
ADC	ADC0_DP1, ADC0_DM1, ADC1_DP1, ADC1_DM1, ADC0_DP0/ADC1_DP3, ADC0_DM0/ADC1_DM3, ADC1_DP0/ADC0_DP3, ADC1_DM0/ADC0_DM3, ADC1_SE16/ADC0_SE22, ADC0_SE16/ADC0_SE21, ADC1_SE18	Ground
DAC [1]	DAC0_OUT, DAC1_OUT	Float
USB	VREGIN, USB0_GND, VOUT33[2]	Connect VREGIN and VOUT33 together and tie to ground through a 10 kΩ resistor. Do not tie directly to ground, as this causes a latch-up risk.
	USB0_DM, USB0_DP	Float

1. Unused DAC signals do not apply to all parts. See the Pinout section for details.
2. USB0_VBUS and USB0_GND are board level signals

5.3 K64 Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

Term	Definition
	• *Operating ratings* apply during operation of the chip. • *Handling ratings* apply when the chip is not powered. **NOTE:** The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.
Operating requirement	A specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip
Operating behavior	A specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions
Typical value	A specified value for a technical characteristic that: • Lies within the range of values specified by the operating behavior • Is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions **NOTE:** Typical values are provided as design guidelines and are neither tested nor guaranteed.

8.2 Examples

Operating rating:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

Operating requirement:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

Operating behavior that includes a *typical value*:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA